AMENDMENTS TO THE CLAIMS

1-15. (Cancelled)

Claim 16. (Currently Amended) A chemical-amplification type silicone-based positive-working resist composition containing:
(A) an alkali-soluble resin which is a ladder-type silicone copolymer containing (a_1) (hydroxyphenylalkyl)silsesquioxane units, (a_2) (alkoxyphenylalkyl)silsesquioxane units wherein the alkoxy group is linear with 1-4 carbon atoms and (a_3) alkyl- or phenylsilsesquioxane units;
(B) a photoacid-generating agent; and
(C) a dissolution inhibitor which is a phenolic or carboxyl compound having the phenolic hydroxyl or carboxyl groups protected with acid-dissociable groups.

Claim 17. (Previously Presented) The chemical-amplification type silicone-based positive-working resist composition described in Claim 16 in which the component (A) is a ladder-type silicone copolymer consisting of 10-70% by moles of the units (a_1), 5-50% by moles of the units (a_2) and 10-60% by moles of the units (a_3).

Claim 18. (Previously Presented) The chemical-amplification type silicone-based positive-working resist composition described in Claim 16 in which the proportion of the units (a_2) is so adjusted that the dissolving rate in alkali be from 0.05 to 50 nm/s.

Claim 19. (Previously Presented) The chemical-amplification type silicone-based positive-working resist composition described in Claim 16 in which the component (B) is an onium salt or a diazomethane compound.

Claim 20. (Previously Presented) The chemical-amplification type silicone-based positive-working resist composition described in Claim 16 wherein the compounding proportion of the

component (C) is from 0.5 to 40 parts by mass per 100 parts by mass of the component (A).

Claim 21. (Previously Presented) The chemical-amplification type silicone-based positive-working resist composition described in Claim 16 which further contains, in addition to the components (A), (B) and (C), (D) a quencher which is an amine compound or an organic acid or both in an amount of 0.01 to 5 parts by mass per 100 parts by mass of the component (A).

Claim 22. (Previously Presented) A bilayered resist material wherein an organic layer is provided on a substrate and a layer of the chemical-amplification type silicone-based positive-working resist composition described in Claim 16 is formed thereon.

Claim 23. (Previously Presented) The bilayered resist material described in Claim 22 in which the organic layer is a layer of a novolak resin or a layer of a novolak resin containing a 1,2-naphthoquinonediazido group.

Claim 24. (Previously Presented) The bilayered resist material described in Claim 22 in which the organic layer has a thickness of 200-800 nm and the layer of the chemical-amplification type silicone-based positive-working resist composition has a thickness of 50-200 nm.

Claim 25. (Currently Amended) A ladder-type silicone copolymer which contains (hydroxyphenylalkyl)silsesquioxane units, (alkoxyphenylalkyl)silsesquioxane units <u>wherein the alkoxy group is linear with 1-4 carbon atoms,</u> and phenylsilsesquioxane units.

Claim 26. (Previously Presented) The ladder-type silicone copolymer described in Claim 25 which consists of 10-70% by moles of the (hydroxyphenylalkyl)silsesquioxane units, 5-50% by moles of the (alkoxyphenylalkyl)silsesquioxane units and 10-60% by moles of the phenylsilsesquioxane units.

Claim 27. (Previously Presented) The ladder-type silicone copolymer described in Claim 25 of which the dissolving rate in alkali is in the range of 0.05-50 nm/s.

Claim 28. (Previously Presented) The ladder-type silicone copolymer described in Claim 25 of which the mass-average molecular weight is in the range of 1500-30000.

Claim 29. (Previously Presented) The ladder-type silicone copolymer described in Claim 25 of which the molecular weight dispersion is in the range of 1.0-5.0.

Claim 30. (Previously Presented) A method of forming a patterned resist film on a substrate which comprises a step of selectively exposing the bilayered resist material described in Claim 22 to actinic rays, and a step of dissolving away the portion of the resist film solubilized by the light-exposure with an aqueous alkali solution.

Claim 31. (New) The chemical-amplification type silicone-based positive-working resist composition of claim 16, wherein the (a_2) units are (methoxyphenylalkyl)silsesquioxane units.

Claim 32. (New) The ladder-type silicone copolymer of claim 25, wherein the (alkoxyphenylalkyl)silsesquioxane units are (methoxyphenylalkyl)silsesquioxane units.